# **Complementary Power Transistors**

# **DPAK For Surface Mount Applications**

Designed for general purpose amplifier and low speed switching applications.

#### **Features**

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("1" Suffix)
- Electrically Similar to Popular TIP41 and TIP42 Series
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V Machine Model, C > 400 V
- Pb-Free Packages are Available

#### **MAXIMUM RATINGS**

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	Vdc
Collector-Base Voltage	V <sub>CB</sub>	100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5	Vdc
Collector Current - Continuous - Peak	I <sub>C</sub>	6 10	Adc
Base Current	Ι <sub>Β</sub>	2	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	20 0.16	W W/°C
Total Power Dissipation (Note 1)  @ T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	71.4	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 These ratings are applicable when surface mounted on the minimum pad sizes recommended.



### ON Semiconductor®

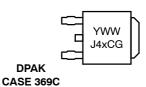
http://onsemi.com

# SILICON POWER TRANSISTORS 6 AMPERES 100 VOLTS, 20 WATTS

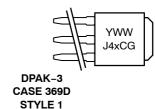
STYLE 1

#### MARKING DIAGRAMS









Y = Year WW = Work Week

J4xC = Device Codex = 1 or 2

#### ORDERING INFORMATION

= Pb-Free Package

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector-Emitter Sustaining Voltage (Note 2) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	100	-	Vdc		
Collector Cutoff Current $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$	I <sub>CEO</sub>	-	50	μAdc		
Collector Cutoff Current (V <sub>CE</sub> = 100 Vdc, V <sub>EB</sub> = 0)	ICES	-	10	μAdc		
Emitter Cutoff Current (V <sub>BE</sub> = 5 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	0.5	mAdc		
ON CHARACTERISTICS (Note 2)	ON CHARACTERISTICS (Note 2)					
DC Current Gain $ \begin{aligned} &(I_C=0.3 \text{ Adc, V}_{CE}=4 \text{ Vdc}) \\ &(I_C=3 \text{ Adc, V}_{CE}=4 \text{ Vdc}) \end{aligned} $	h <sub>FE</sub>	30 15	- 75	-		
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 6 Adc, I <sub>B</sub> = 600 mAdc)	V <sub>CE(sat)</sub>	-	1.5	Vdc		
Base–Emitter On Voltage ( $I_C = 6$ Adc, $V_{CE} = 4$ Vdc)	V <sub>BE(on)</sub>	-	2	Vdc		
DYNAMIC CHARACTERISTICS				-		
Current Gain – Bandwidth Product (Note 3) (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1 MHz)	f <sub>T</sub>	3	_	MHz		
Small-Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1 kHz)	h <sub>fe</sub>	20	_	-		

<sup>2.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%. 3.  $f_T = |h_{fe}| \bullet f_{test}$ .

#### **ORDERING INFORMATION**

Device	Package Type	Package	Shipping <sup>†</sup>	
MJD41CRL	DPAK			
MJD41CRLG	DPAK (Pb-Free)	]	1800 / Tape & Reel	
MJD41CT4	DPAK		2500 / Tape & Reel	
MJD41CT4G	DPAK (Pb-Free)	369C		
MJD42C	DPAK		- 75 Units / Rail	
MJD42CG	DPAK (Pb-Free)			
MJD42C1	DPAK-3			
MJD42C1G	DPAK-3 (Pb-Free)	369D		
MJD42CRL	DPAK	369C	1800 / Tape & Reel	
MJD42CRLG	DPAK (Pb-Free)			
MJD42CT4	DPAK			
MJD42CT4G	DPAK (Pb-Free)		2500 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### TYPICAL CHARACTERISTICS

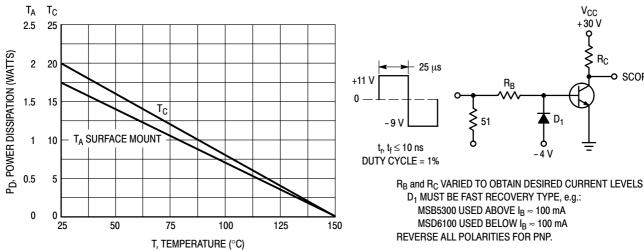
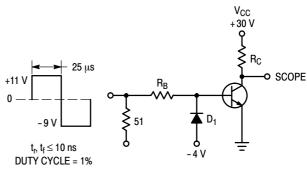


Figure 1. Power Derating

MSD6100 USED BELOW  $I_B \approx 100 \ mA$ REVERSE ALL POLARITIES FOR PNP.



D<sub>1</sub> MUST BE FAST RECOVERY TYPE, e.g.: MSB5300 USED ABOVE  $I_B \approx 100 \text{ mA}$ 

Figure 2. Switching Time Test Circuit

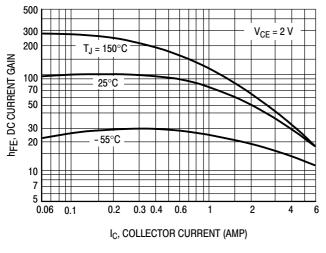


Figure 3. DC Current Gain

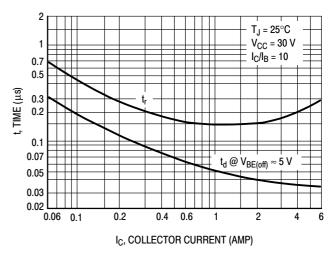


Figure 4. Turn-On Time

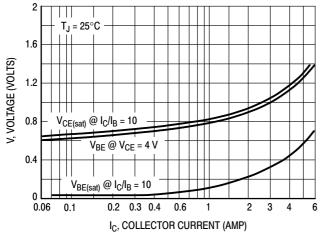


Figure 5. "On" Voltages

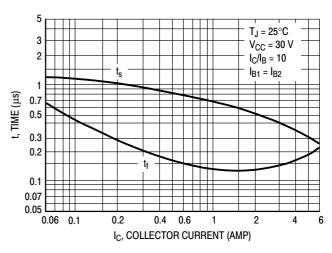


Figure 6. Turn-Off Time

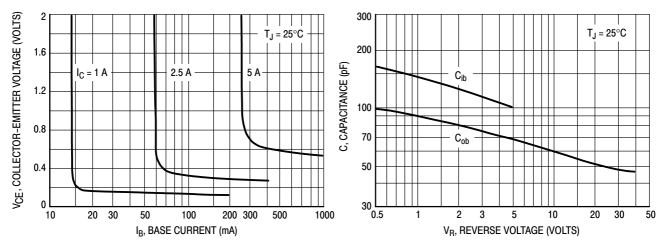


Figure 7. Collector Saturation Region

Figure 8. Capacitance

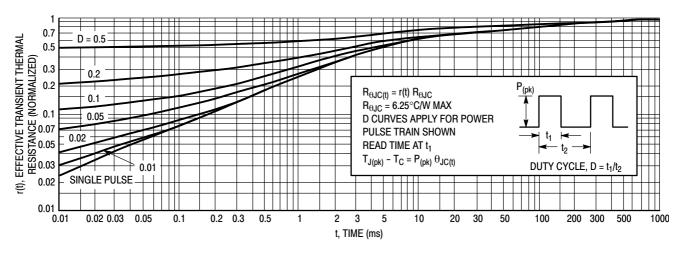


Figure 9. Thermal Response

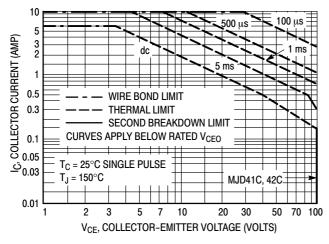


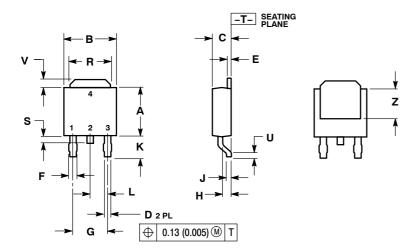
Figure 10. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 10 is based on  $T_{J(pk)}=150^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 9. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

#### PACKAGE DIMENSIONS

#### **DPAK** CASE 369C **ISSUE O**

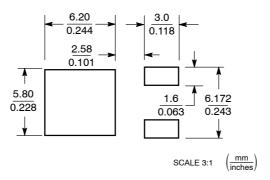


- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.22
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020		0.51	
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

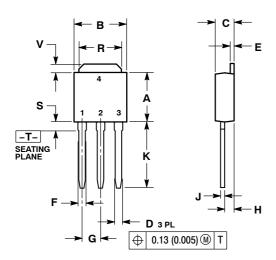
#### **SOLDERING FOOTPRINT\***

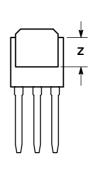


\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

DPAK-3 CASE 369D-01 **ISSUE B** 





#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
Е	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		C 2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
Κ	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

STYLE 1: PIN 1. BASE

2. COLLECTOR

3. EMITTER 4. COLLECTOR

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and war engineer trademarks of semiconductor components industries, Ite (SciLLC) solitate services are injective to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative